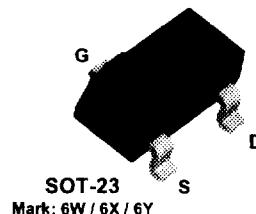
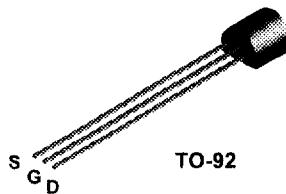


**J174****J175****J176****J177****MMBFJ175****MMBFJ176****MMBFJ177**

## P-Channel Switch

This device is designed for low level analog switching sample and hold circuits and chopper stabilized amplifiers. Sourced from Process 88.

### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>DG</sub>	Drain-Gate Voltage	- 30	V
V <sub>GS</sub>	Gate-Source Voltage	30	V
I <sub>GF</sub>	Forward Gate Current	50	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\* These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		J174 - J177	*MMBFJ175	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	350 2.8	225 1.8	mW mW/°C
R <sub>RJC</sub>	Thermal Resistance, Junction to Case	125		°C/W
R <sub>RAA</sub>	Thermal Resistance, Junction to Ambient	357	556	°C/W

\* Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

**P-Channel Switch**

(continued)

**Electrical Characteristics**

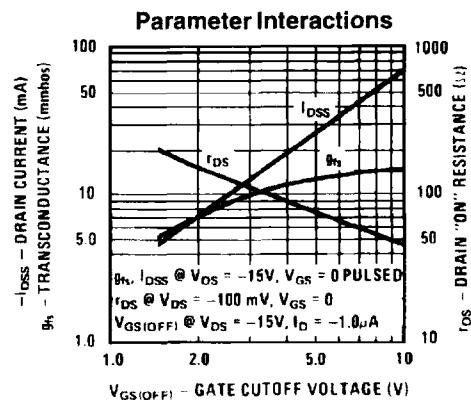
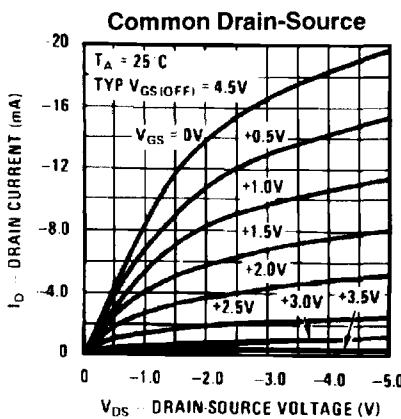
TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
<b>OFF CHARACTERISTICS</b>					
B <sub>(BR)GSS</sub>	Gate-Source Breakdown Voltage	I <sub>G</sub> = 1.0 μA, V <sub>DS</sub> = 0	30		V
I <sub>GSS</sub>	Gate Reverse Current	V <sub>GS</sub> = 20 V, V <sub>DS</sub> = 0		1.0	nA
V <sub>GS(off)</sub>	Gate-Source Cutoff Voltage	V <sub>DS</sub> = -15 V, I <sub>D</sub> = -10 nA	J174 J175 J176 J177	5.0 3.0 1.0 0.8	V
				10 6.0 4.0 2.5	V
					V

**ON CHARACTERISTICS**

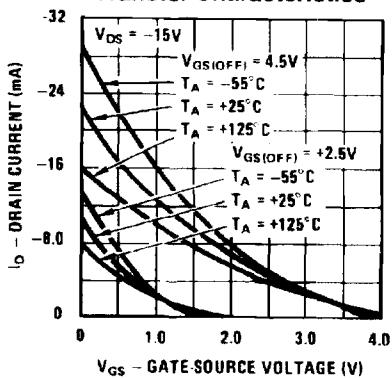
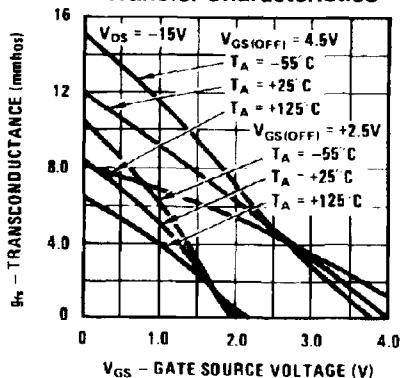
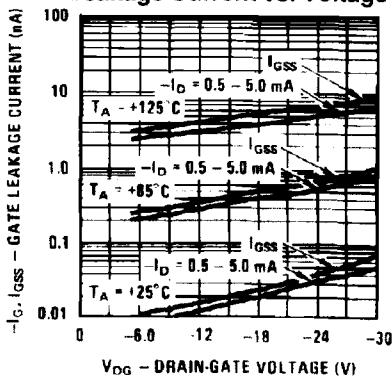
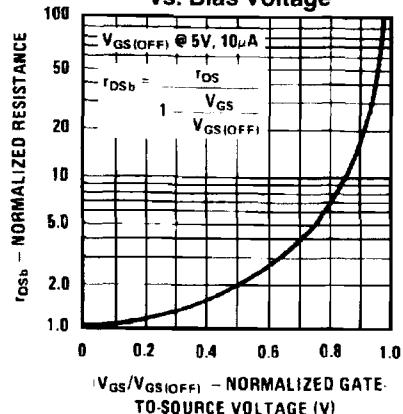
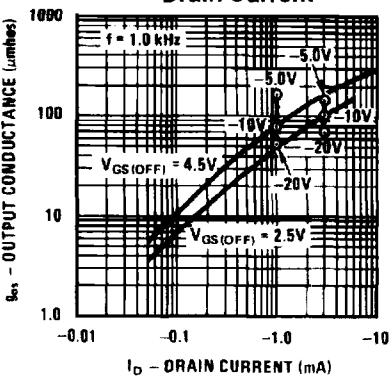
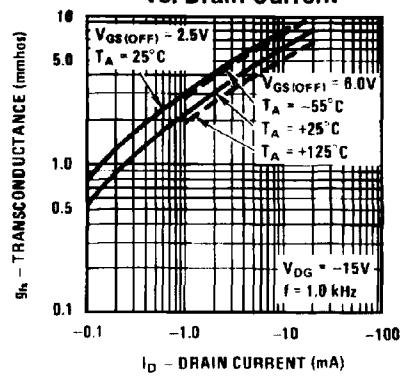
I <sub>DSS</sub>	Zero-Gate Voltage Drain Current*	V <sub>DS</sub> = -15 V, I <sub>GS</sub> = 0	J174 J175 J176 J177	-20 -7.0 -2.0 -1.5	-100 -60 -25 -20	mA
r <sub>D(on)</sub>	Drain-Source On Resistance	V <sub>DS</sub> ≤ 0.1 V, V <sub>GS</sub> = 0	J174 J175 J176 J177		85 125 250 300	Ω

\*Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

**Typical Characteristics**

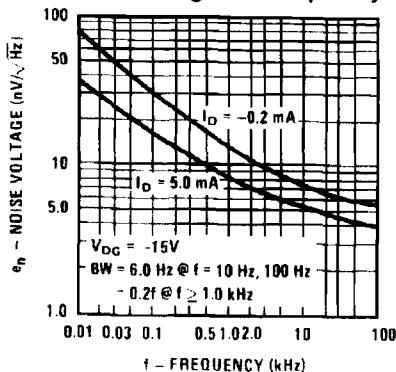
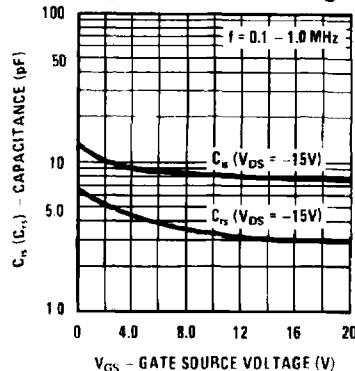
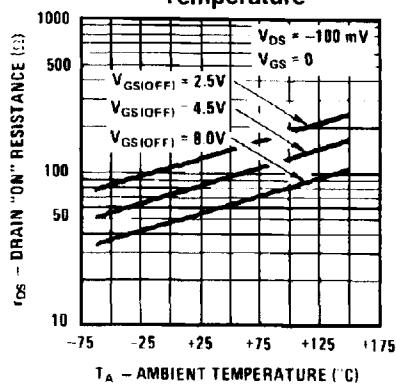
**P-Channel Switch**

(continued)

**Typical Characteristics** (continued)**Transfer Characteristics****Transfer Characteristics****Leakage Current vs. Voltage****Normalized Drain Resistance vs. Bias Voltage****Output Conductance vs. Drain Current****Transconductance vs. Drain Current**

**P-Channel Switch**

(continued)

**Typical Characteristics** (continued)**Noise Voltage vs. Frequency****Capacitance vs. Voltage****Channel Resistance vs. Temperature****POWER DISSIPATION VS AMBIENT TEMPERATURE**